

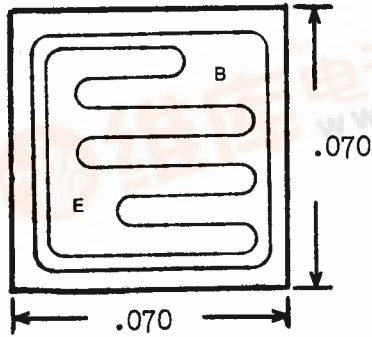
X00020

TR0006

ACTIVE

STX 7904 / ~~7905~~ CHIP

HIGH VOLTAGE **NPN** TRANSISTOR
MESA PASSIVATED



Contact Area: .014 x .018

CONTACT METALLIZATION

Base/Emitter: > 30,000 Å Aluminum
Collector: > 2,000 Å Evaporated Gold

ASSEMBLY RECOMMENDATIONS

1. Eutectic Die Attach.
2. Ultrasonically Attach 5 MIL Aluminum Wire To Base/Emitter Contacts.

PARAMETER	TEST CONDITIONS *	TYPE	MIN.	MAX.	UNIT
BV _{CEO}	IC=1mA	STX 7904	350		Vdc
		STX 7905	400		Vdc
BV _{CBO}	IC=100uA	STX 7904	500		Vdc
		STX 7905	600		Vdc
BV _{CER}	IC=100uA, RBE=1KOhm	STX 7904	500		Vdc
		STX 7905	600		Vdc
BV _{EBO}	IE=20uA	ALL	10		Vdc
t _{EBO}	VEB=10V	ALL		50	u Adc
I _{CBO}	VCB=500V	STX 7904		50	u Adc
	VCB=600V	STX 7905		50	u Adc
h _{FE}	VCE=5V, IC=500mA		20	65	
h _{FE}	VCE=5V, IC=25mA		20	300	
h _{FE}	VCE=5V, IC=1mA		20	250	
V _{BE(SAT)}	IC=500mA, IB=100mA			1.0	Vdc
V _{CE(SAT)}	IC=500mA, IB=100mA			500	mVdc
C _{OB}	VCB=15V, f=2MHZ			20	pf
h _{fe}	VCE=10V, IC=50mA, f=5MHZ		2		

* Electrical characteristics measured at lot acceptance testing in a TO-5 package. Specifications subject to change without notice.

